Contribution ID: 41

Type: Standard (20 min including discussion)

## **T-CAD** simulation of Lorentz angle

Thursday 14 November 2013 17:25 (20 minutes)

T-CAD simulations are a powerful tool for understanding the properties of silicon sensors. Silvaco T-CAD allows the implementation of magnetic fields of several Tesla in the simulation. Using this simulation package, Lorentz angle measurements on strip sensors have been reproduced. Results on non-irradiated devices and the ongoing work of implementing radiation damage using an effective trap model will be presented.

Primary author: NURNBERG, Andreas Matthias (KIT - Karlsruhe Institute of Technology (DE))

**Co-authors:** DIERLAMM, Alexander (KIT - Karlsruhe Institute of Technology (DE)); Prof. MULLER, Thomas (KIT - Karlsruhe Institute of Technology (DE)); DE BOER, Wim (KIT - Karlsruhe Institute of Technology (DE))

Presenter: NURNBERG, Andreas Matthias (KIT - Karlsruhe Institute of Technology (DE))

Session Classification: Device Simulations and some key experimental data